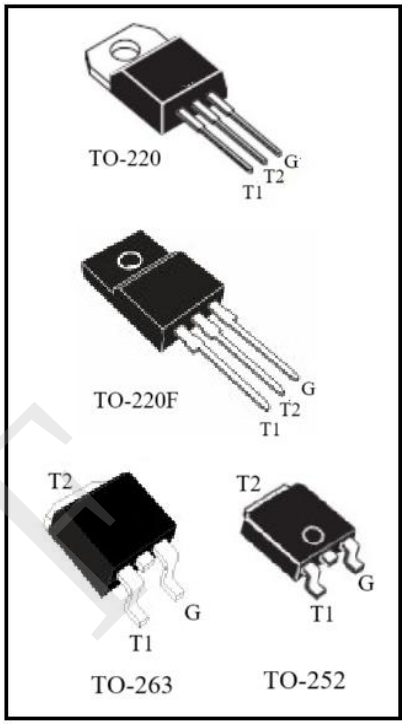
鼎德丰
DING DE FENG

TRIAC BTB06

FEATURES

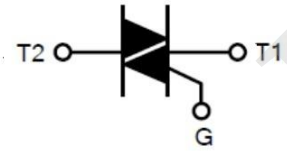
- Planar passivated for voltage ruggedness and reliability
- Low gate trigger current
- Low holding current
- High thermal cycling performance
- High voltage capability
- High current surge capability



APPLICATIONS

- Mains power AC switching
- Static relays
- Light dimmers
- Heater Control
- Motor Speed Controller

SYMBOL:



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE		UNIT
Repetitive Peak Off-State Voltages	V_{DRM}, V_{RRM}	BTB06-600(C/B)	600	V
		BTB06-800(C/B)	800	
RMS on-State Current	$I_{T(RMS)}$	6		A
Non-Repetitive Peak On-State Current	I_{TSM}	60		A
I^2t for fusing	I^2t	21		A^2s
Repetitive rate of rise of on-state current after triggering	di/dt	50		A/uS
Peak gate current	I_{GM}	4		A
Average Gate Power	$P_{G(AV)}$	1		W
Operating junction temperature	T_J	-40~+125		℃
Storage Temperature	T_{STG}	-40 ~ +150		℃

ELECTRICAL CHARACTERISTICS (TJ=25°C)

Parameter	Symbol	Test Conditions		MIN	MAX		Units
					C	B	
Peak Repetitive Forward or Reverse Blocking Current	I_{DRM} I_{RRM}	V_{AK} = Rated V_{DRM} or V_{RRM};			5		uA
Gate Trigger Current	I_{GT}	V_D=12V, R_L=33Ω	I		25	50	mA
			II		25	50	
			III		25	50	
			IV		50	100	
Gate Trigger Voltage	V_{GT}	V_D=12V, R_L=33Ω			1.5		V
Gate Non−Trigger Voltage	V_{GD}	V_D = V_{DRM}, R_L = 3.3 kΩ, T_j = 125 °C		0.2			V
Peak Forward On-State Voltage	V_{TM}	IT=8.5A,			1.55		V
Latch Current	I_L	IG=1.2IGT	I		40	50	mA
			II		80	100	
			III		40	50	
			IV		40	50	
Holding Current	I_H	IT=0.1A			25	50	mA
Critical Rate of Rise of Off-State Voltage	dV/dt	V_D=67%V_{DRM}, T_J=25°C, Gate open		200			V/μs